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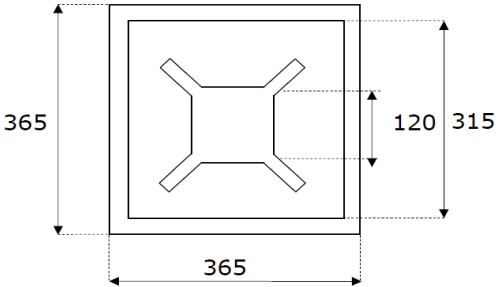
Data Sheet

LED Chip Infrared

EOLC-905-17

Rev. 03, 2017

Radiation	Type	Electrodes
Infrared	AlGaAs/AlGaAs, DDH	P (anode) up

	typ. dimension (μm) typ. thickness 150 ± 25 μm anode - gold alloy, 1.5 μm cathode - gold alloy, 0.5 μm, structured, 25% covered
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Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F =20 mA	V _F		1.3	1.5	V
Reverse voltage	I _R =100 μA	V _R	5			V
Radiant power*	I _F =20 mA	Φ _e	3	4		mW
Radiant power**	I _F =20 mA	Φ _e		8		mW
Peak wavelength	I _F =20 mA	λ _p	895	905	915	nm
FWHM	I _F =20 mA	Δλ _{0.5}		55		nm
Switching time	I _F =20 mA	t _r , t _f		400		ns

*Measured on bare chip on TO-18 header

**Measured on epoxy covered chip on TO-18 header

Packing

Chips on adhesive film with wire-bond side top

Art. No. 113 024



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.